

FEATURES

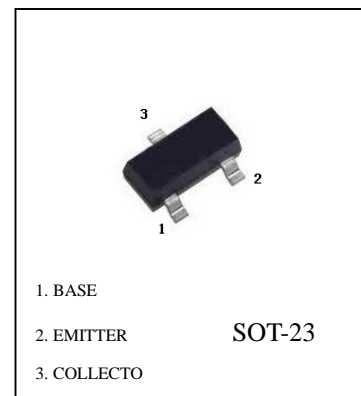
Complimentary to S8550

MARKING: J3Y

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	0.5	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to +150	℃

S8050 (NPN)



ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = 100\mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = 100\mu A, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40V, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB} = 20V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE} = 1V, I_C = 50mA$	120		350	
	$H_{FE(2)}$	$V_{CE} = 1V, I_C = 500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA$			1.2	V
Transition frequency	f_T	$V_{CE} = 6V, I_C = 20mA$ $f = 30MHz$	150			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H	
Range	120-200	200-350	

S8050 Typical Characteristics

